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NTE96 Silicon NPN Transistor Power Switching

Absolute Maximum Ratings:

Collector-Base Voltage, V_{CBO}	100V
Collector-Emitter Voltage, V_{CEO}	100V
Emitter-Base Voltage, V_{EBO}	6V
Collector Current, I_C	7A
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	60W
Operating Junction Temperature Range, $T_{j(\text{oper})}$	-65° to $+200^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+200^\circ\text{C}$

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Typical Forward Current Gain	h_{FE}	$I_C = 2A, V_{CE} = 2V$	60	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(\text{SAT})}$	$I_C = 7A, I_B = 0.7A$	-	1.2	-	V
Transition Frequency	f_T		30	-	-	MHz

